

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1	hocheng near hong.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 1 14:27
2	BRS	L2	0	huang near yun- liang.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 1 14:28
3	BRS	L3	2004	438/692.ccls.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 1 14:29

	Type	L #	Hits	Search Text	DBs	Time Stamp
4	BRS	L4	271	3 and (endpoint or end-point)	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2004/12/01 14:30
5	BRS	L6	0	3 and (endpoint or end-point) near5 (cmp) near15 (slope)	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2004/12/01 14:33
6	BRS	L5	129	3 and (endpoint or end-point) near5 cmp	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2004/12/01 14:31

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L7	3	3 and (endpoint or end-point) near5 (cmp) near15 (temp)	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2004/12/01 14:34
8	BRS	L8	3	3 and (endpoint or end-point) near5 (cmp) near15 (temperature)	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2004/12/01 14:35
9	BRS	L9	0	3 and (slope) near5 (cmp) near15 (temperature)	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2004/12/01 14:35

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L10	0	(slope) near5 (cmp) near15 (temperature)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 1 14:35
11	BRS	L11	0	(slope) near25 (cmp) near15 (temperature)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 1 14:35
12	BRS	L12	18	(endpoint or end- point) near5 (cmp) near15 (temperature)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 1 14:35

	U	1	Document ID	Title	Current OR
1			US 20040080757 A1	Integrated surface metrology	356/601
2			US 20030077995 A1	Chemical mechanical polishing slurry	451/528
3			US 20030045100 A1	In-situ method and apparatus for end point detection in chemical mechanical polishing	438/689
4			US 20020173252 A1	Chemical mechanical polishing	451/259
5			US 20020023338 A1	Method for making a magnetoresistive sensor	29/603.15
6			US 20020022372 A1	Method for reducing micro-particle adsorption effects	438/692
7			US 6798529 B2	In-situ method and apparatus for end point detection in chemical mechanical polishing	356/630
8			US 6690473 B1	Integrated surface metrology	356/601
9			US 6676492 B2	Chemical mechanical polishing.	451/65
10			US 6517413 B1	Method for a copper CMP endpoint detection system	451/6
11			US 6503124 B1	Method for endpoint detection for copper CMP	451/6

	U	1	Document ID	Title	Current OR
12			US 6479387 B2	Method for reducing micro-particle adsorption effects	438/692
13			US 6458017 B1	Planarizing method	451/28
14			US 6179691 B1	Method for endpoint detection for copper CMP	451/41
15			US 5647952 A	Chemical/mechanical polish (CMP) endpoint method	438/8
16			US 5597442 A	Chemical/mechanical planarization (CMP) endpoint method using measurement of polishing pad temperature	438/8
17			US 5196353 A	Method for controlling a semiconductor (CMP) process by measuring a surface temperature and developing a thermal image of the wafer	438/5

	U	1	Document ID	Title	Current OR
18			TW 299462 A	Polishing endpoint detection method for CMP - using IR temperature detection device to detect change of temperature at endpoint when removing one material and exposing second material	